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## Nota di contenuto

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## Sommario/riassunto

This book takes the reader through the actual manufacturing process of making a typical chip, from start to finish, including a detailed discussion of each step, in plain language. The evolution of today's technology is added to the story, as seen through the eyes of the engineers who solved some of the problems. The authors are well suited to that discussion since they are three of those same engineers. They have a broad exposure to the industry and its technology that extends all the way back to Shockley Laboratories, the first semiconductor manufacturer in Silicon Valley.The CMOS (C